U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SNDK.327US0	10/774,014
	Applicants	Conf. No.
(Use several sheets if necessary)	Gerrit Jan HEMINK	8419
(Form PTO-1449)	Filing Date	Art Group
	February 6, 2004	2827

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Examiner	/Michael Tran/	Date Considered	07/07/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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